EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L10	22	L5 AND L8	US-PGPUB; USPAT	OR	OFF	2006/03/31 11:50
L8	13853	((438/5,9,14,16,714,719,720,721, 723,724,725,740,743,744) or (216/60,67,79) or (430/5)).CCLS.	US-PGPUB; USPAT	OR	OFF	2006/03/31 11:49
L3	13383	((438/5,9,14,16,714,719,720,721, 723,724,740,743,744) or (216/60, 67,79) or (430/5)).CCLS.	US-PGPUB; USPAT	OR	OFF	2006/03/31 11:47
L7	13	L4 AND (post$1etch$4 NEAR20 (residue$4 OR polymer$4))	US-PGPUB	OR	OFF	2006/03/31 11:45
L6	1	L4 AND (post$1etch$4 NEAR20 (residue$4 OR polymer$4) NEAR20 thickness$4)	US-PGPUB; USPAT	OR	OFF	2006/03/31 11:45
L5	50	L4 AND (post$1etch$4 NEAR20 (residue$4 OR polymer$4))	US-PGPUB; USPAT	OR	OFF	2006/03/31 11:45
L4	129284	(field$4 NEAR3 effect$4 NEAR3 transistor$4) OR FET OR MOS$1FET	US-PGPUB; USPAT	OR	OFF	2006/03/31 11:44
S43	13	S42 AND (side$1wall$4 NEAR20 (residue$4 OR polymer$4))	US-PGPUB; USPAT	OR	OFF	2006/03/31 11:43
S42	1802	S41 AND ((resist$4 OR photo$1resist$4) NEAR20 trim$4)	US-PGPUB; USPAT	OR	OFF	2006/03/31 11:19
S36	12762	((438/5,9,14,16,714,719,720,721, 723,724,740,743,744) or (216/60, 67,79) or (430/5)).CCLS.	US-PGPUB; USPAT	OR	OFF	2006/03/31 11:19
L2	80	L1 AND ((resist$4 OR photo$1resist$4) NEAR20 trim$4)	EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/31 11:19
S41	129284	(field$4 NEAR3 effect$4 NEAR3 transistor$4) OR FET OR MOS$1FET	US-PGPUB; USPAT	OR	OFF	2006/03/31 11:18
L1	107957	(field$4 NEAR3 effect$4 NEAR3 transistor$4) OR FET OR MOS$1FET	EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/31 11:18
S30	123535	(field$4 NEAR3 effect$4 NEAR3 transistor$4) OR FET OR MOS$1FET	US-PGPUB; USPAT	OR	OFF	2006/03/30 18:06
S40	12	S39 AND etch$4 AND (((hydrogen$4 ADJ bromide$4) OR HBr) WITH (chlori$4 OR Cl2 OR "Cl.sub.2"))	EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/09 11:34
S39	106004	(field$4 NEAR3 effect$4 NEAR3 transistor$4) OR FET OR MOS$1FET	EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/09 11:34

S38	22	S35 AND S36	US-PGPUB; USPAT	OR	OFF	2005/11/09 11:34
S31	854	S30 AND etch$4 AND (((hydrogen$4 ADJ bromide$4) OR HBr) WITH (chlori$4 OR Cl2 OR "Cl.sub.2"))	US-PGPUB; USPAT	OR	OFF	2005/11/09 11:34
S35	112	S33 AND (optical$4 OR scatteromet$4)	US-PGPUB; USPAT	OR	OFF	2005/11/09 11:33
S27	67	S26 AND (optical$4 OR scatteromet$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/09 11:33
S22	18764	((438/5,9,14,16,714,719,720,721, 723,724,740,743,744) or (216/60, 67,79) or (430/5)).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/09 11:33
S33	483	S32 AND poly$1silicon	US-PGPUB; USPAT	OR	OFF	2005/11/09 11:32
S26	336	S25 AND poly$1silicon	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/09 11:32
S32	516	S31 AND side$1wall$4	US-PGPUB; USPAT	OR	OFF	2005/11/09 11:31
S25	354	S24 AND side$1wall$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/09 11:31
S24	559	S23 AND etch$4 AND (((hydrogen$4 WITH bromide$4) OR HBr) WITH (chlori$4 OR Cl2 OR "Cl.sub.2"))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/09 11:30
S23	122238	field$4 WITH effect$4 WITH transistor$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/09 11:29

S28	9	S22 AND S27	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/21 09:40
S1	8	((("5,926,690") or ("5,948,203") or ("6,161,054") or ("6,245,581") or ("6,424,417") or ("6,479,309") or ("6,486,492") or ("6,501,555")).PN. or ((2002/0171828) or (2002/0072003) or (2003/0000922)).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2005/06/21 09:37
S20	1	("20050064714").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2005/06/20 16:56
S12	4	S11 AND (optical$4 WITH scatteromet$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/20 16:56
S19	1	("5912741").PN.	USPAT; USOCR	OR	OFF	2005/06/20 16:32
S18	58	S17 AND ((nitrogen OR N2 OR "N.sub.2") WITH (hydrogen OR H2 OR "H.sub.2") WITH (oxygen OR O2 OR "O.sub.2"))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/20 16:32
S17	559	S16 AND etch$4 AND (((hydrogen$4 WITH bromide$4) OR HBr) WITH (chlori$4 OR Cl2 OR "Cl.sub.2"))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/20 14:37
S16	122165	field$4 WITH effect$4 WITH transistor$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/20 14:37
S15	6	S14 AND (optical$4 WITH scatteromet$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/20 12:58

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S14	315	S13 AND side$1wall$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/20 12:58
S5	354	S3 AND side$1wall$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/20 12:58
S13	2861	S2 AND (trim$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/20 12:57
S11	1131	S2 AND (trim$4 WITH (photo$1resist$4 OR mask$4 OR resist$4))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/20 12:57
S9	2	S6 AND (optical$4 WITH scatteromet$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/20 12:08
S7	23	S6 AND (trim$4 WITH (photo$1resist$4 OR mask$4 OR resist$4))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/20 12:07
S10	9	S7 AND (optical$4 OR scatteromet$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/20 11:55
S8	67	S6 AND (optical$4 OR scatteromet$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/20 11:55

S6	336	S5 AND poly$1silicon	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/20 11:28
S3	559	S2 AND etch$4 AND (((hydrogen$4 WITH bromide$4) OR HBr) WITH (chlori$4 OR Cl2 OR "Cl.sub.2"))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/20 11:25
S2	122165	field$4 WITH effect$4 WITH transistor$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/20 11:22